

Converting Resistivity to Carrier Concentration

Spreading Resistance Analysis (SRA) determines a resistivity-depth profile in silicon. To calculate carrier concentration values, we use carrier mobility values derived from Thurber, Mattis, Liu, and Filliben, National Bureau of Standards Special Publication 400-64, *The Relationship Between Resistivity and Dopant Density for Phosphorus-and Boron-Doped Silicon* (May 1981), Table 10, Page 34 and Table 14, Page 40. We hope you find the following chart useful.

